

Summary of Liverpool CC(V) Measurements

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Purpose of this Talk

- Summarize all the charge collection measurements made at Liverpool with RD50 4" and 6" wafers
 - Some shown at previous RD50 meetings
 - Some at other conferences
 - Some are new measurements
 - Also have more extensive ATLAS07 HPK and VELO test structure results to compare with
- Wanted to provide one location to find our latest data and updated papers

Apologizes if you seen these previously



Miniature Silicon Micro-strip Sensors

Microstrip, \sim 1x1 cm², 100-128 strips, 75-80 µm pitch

Micron/RD50 4" & 6" wafers (300 μ m)

•n-in-p FZ (V_{FD} ~15V/~70 V)

•n-in-n FZ (V_{FD}~10 V)

•p-in-n FZ (V_{FD} ~10V)

Micron/RD50 4" (500 μm) Micron/RD50 4" (140 um)

•n-in-p FZ (V_{FD}~350 V

•n-in-p MCz (V_{FD}~550 V)

•n-in-n MCz (V_{FD}~170 V)

•p-in-n MCz (V_{FD} ~170 V)

•n-in-p FZ (VFD~2-10 V)

CNM RD50 EPI miniatures (~150 μm active)

•p-in-n EPI

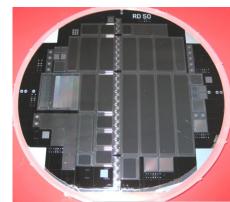
•n-in-p EPI

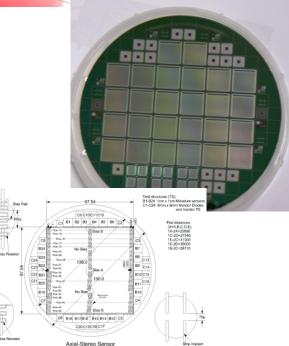
Micron/VELO test structures (~300 μ m)

•n-in-n FZ (V_{FD} ~70V)

ATLAS07 HPK test structures (~310 mm)

•n-in-p FZ (V_{FD}~150-200 V)



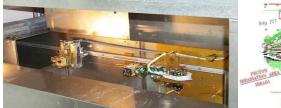


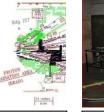


Irradiation Sources



Irradiation and dosimetry (Neutrons): Triga Reactor, Jozef Stefan Institute, Ljubljana, Slovenia: <u>V. Cindro, et. al.</u>

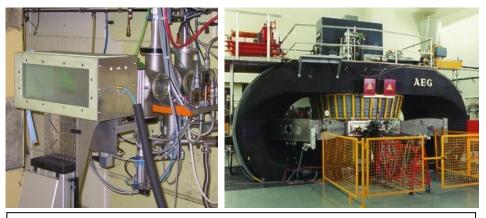




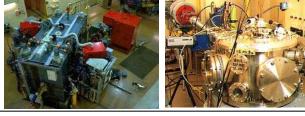
Irradiation and dosimetry (24 GeV Protons): CERN PS Irrad1 facility, Geneva Switzerland: <u>M. Glaser, et. al</u>.



Irradiation and dosimetry (280 MeV/c Pions): Paul Scherrer Institut, Switzerland: <u>M. Glaser, T. Rohe, et. al.</u>



Irradiation and dosimetry (26 MeV Protons): Compact Cyclotron, Karlsruhe, Germany: <u>W. de Boer, A. Dierlamm, et. al.</u>

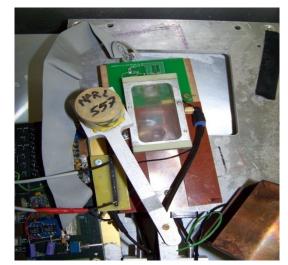


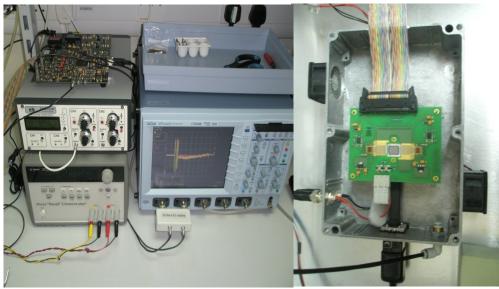
Irradiation and dosimetry (70 MeV Protons): AVF Cyclotron at CYRIC, Sendai, Japan: Y. Unno, T. Shinozuka, et. al.



Experimental Setups

- Charge collection efficiency (CCE) measured using an analogue electronics chips (SCT128 or Beetle) clocked at LHC speed (40MHz clock, ~25ns shaping time).
 - Measurements performed n chest freezer at a temperature of ~-25 °C with N₂ flush
- ⁹⁰Sr fast electron source triggered with scintillators in coincidence used to generate signal.
- The system is calibrated to the most probable value of the MIP energy loss in a non-irradiated 300µm thick detector (~23000 e⁻)

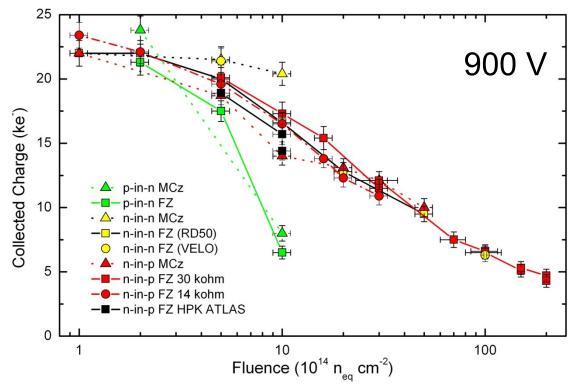






Neutron Summary

- After ~5×10¹⁴ n cm⁻², n-in-n FZ, n-in-p FZ, n-in-p MCz very similar
- At higher voltage, n-in-n MCz superior up to maximum fluence (10¹⁵ n cm⁻²)
 - Still need higher fluence. Detectors for irradiation in hand
- HPK and Micron consistent

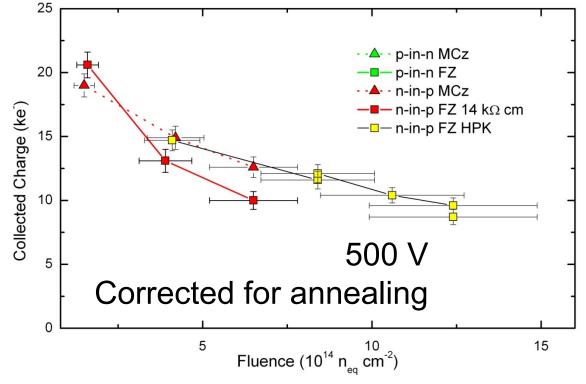


<u>Micron:</u> shown at RESMDD08, Florence, 15th-17th October 2008
 published A. Affolder, et. al., Nucl. Instr. Meth. A, Vol. 612 (2010), 470-473.
 <u>HPK:</u> shown HSTD7 Hiroshima, 28th Aug-1st Sept 2009
 published K. Hara, et. at., Nucl. Inst. Meth. A, Vol. 636 (2011) S83-S89.

All n-strip readout choices studied are the same after neutron irradiation once effects of "active" base and multiplication dominant

Pion Summary

- Interpretation of pion data made more problematic by annealing during irradiations
 - For Micron data, up to 13 days at 24 C
 - For HPK data, up to
 12.5 days at 26 C

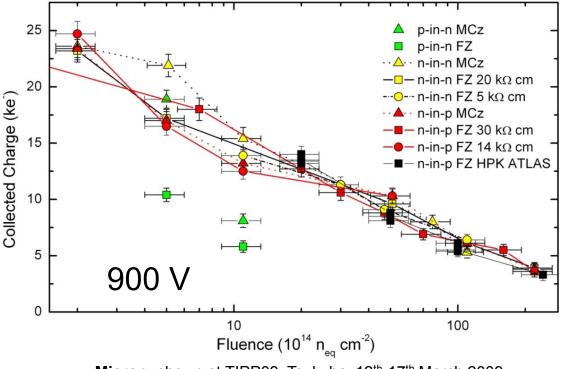


<u>Micron:</u> shown at TIPP09, Tsukuba, 12th-17th March 2009 published A. Affolder, et. al., Nucl. Instr. Meth. A, Vol.623 (2010), 177-179. <u>HPK:</u> New and unpublished

Results similar to neutron measurements after removing effects of annealing during irradiation

26 MeV Proton Summary

- Above 1×10¹⁵ n_{eq} cm⁻², all n-strip readout devices give similar results
 - All 2×10¹⁴ n_{eq} cm⁻² and all n-in-n MCz except 1×10¹⁵ n_{eq} cm⁻² new and unpublished
- HPK and Micron also consistent within uncertainties



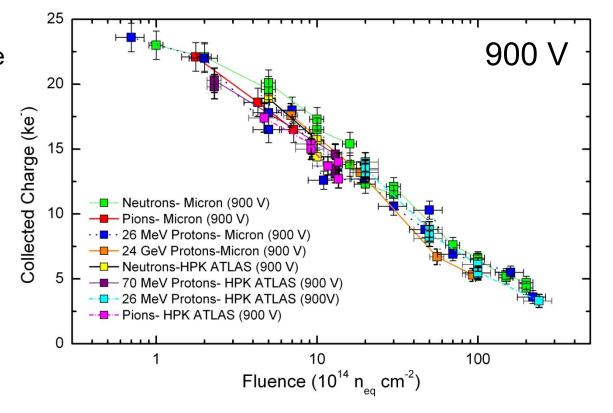
<u>Micron:</u> shown at TIPP09, Tsukuba, 12th-17th March 2009 published A. Affolder, et. al., Nucl. Instr. Meth. A, Vol.623 (2010), 177-179. <u>HPK:</u> shown at 5th Trento Workshop (2010) and unpublished

Once "active" base and multiplication dominates, all n-strip readout choices studied are the same after 26 MeV protons irradiation as well



n-in-p FZ Irradiation Summary

- After reducing the measured collected charge after pion and 70 MeV proton irradiations to remove estimated annealing during irradiation/shipment, all sources give consistent CCE vs. fluence within uncertainties
 - NIEL looks really good!!
 - Micron and HPK produced sensors also give really consistent results!!!



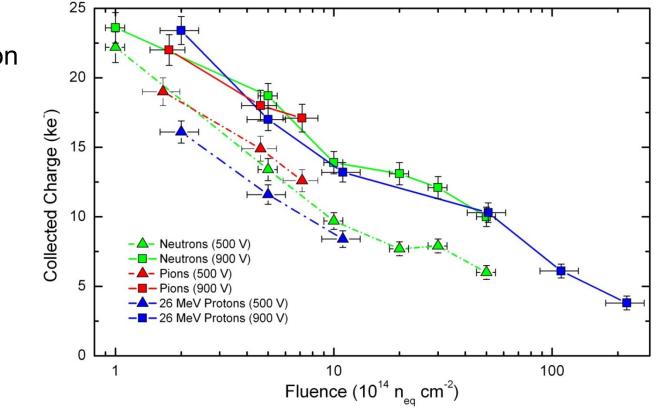
Micron: shown at TIPP09, Tsukuba, 12th-17th March 2009 published A. Affolder, et. al., Nucl. Instr. Meth. A, Vol. 623 (2010), 177-179.

<u>HPK:</u> Neutrons and 70 MeV protons shown HSTD7 Hiroshima, 28th Aug-1st Sept 2009 26 MeV protons shown at 5th Trento Workshop; pions new results Neutrons and 70 MeV protons published K. Hara, et. at., Nucl. Inst. Meth. A, Vol. 636 (2011) S83-S89.



n-in-p MCz Irradiation Summary

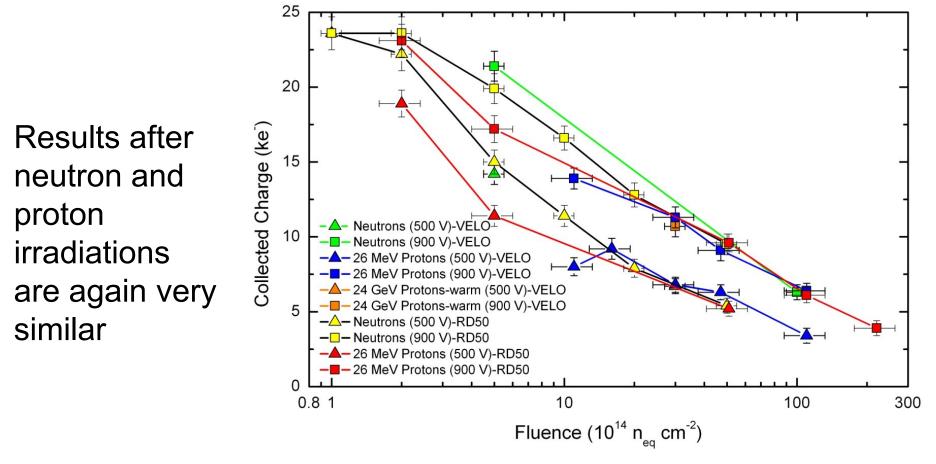
- After reducing the pion CCE to remove estimated annealing during irradiation, all sources give consistent CCE vs. fluence within uncertainties
 - NIEL looks good again!!



Shown at TIPP09, Tsukuba, 12^{th} - 17^{th} March 2009 Published: A. Affolder, et. al., Nucl. Instr. Meth. A, Vol.623 (2010), 177-179. $2 \times 10^{14} n_{eq} \text{ cm}^{-2} 26 \text{ MeV RD50}$ new and unpublished



n-in-n FZ Irradiation Summary

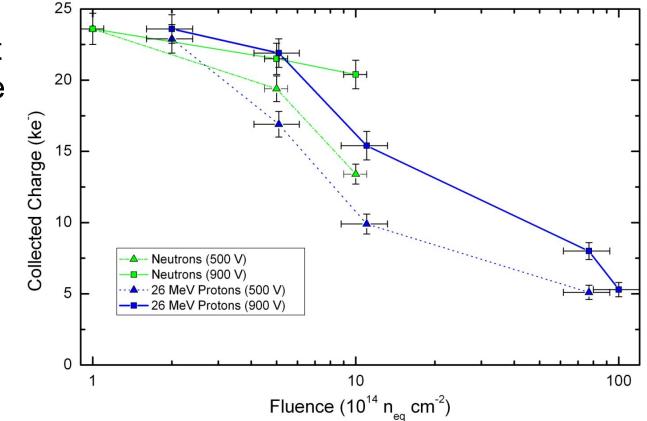


Shown at TIPP09, Tsukuba, 12th-17th March 2009 Published: A. Affolder, et. al., Nucl. Instr. Meth. A, Vol.623 (2010), 177-179. 2×10¹⁴ n_{eq} cm⁻² 26 MeV RD50 & 11 and 110×10¹⁴ n_{eq} cm⁻² 26 MeV VELO data new and unpublished



n-in-n MCz Irradiation Summary

There are signs that n-in-n MCz might be the most radiation hard material up to $1 \times 10^{15} n_{eq} \text{ cm}^{-2}$. More study is still needed especially after mixed irradiations.

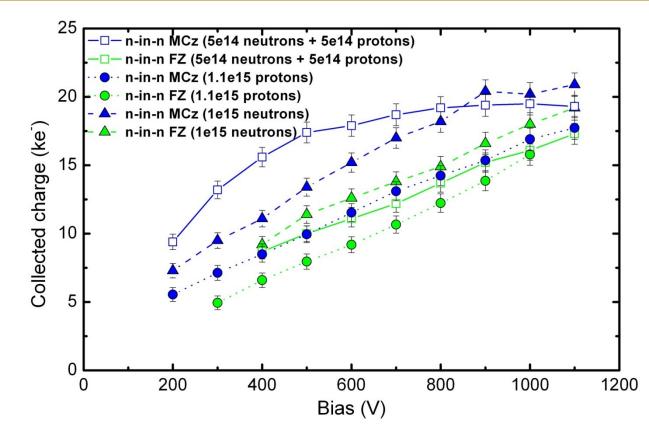


Shown at TIPP09, Tsukuba, 12th-17th March 2009 Published: A. Affolder, et. al., Nucl. Instr. Meth. A, Vol.623 (2010), 177-179. All 26 MeV protons except 1×10¹⁵ n_{eq} cm⁻² new and unpublished



Mixed Irradiations

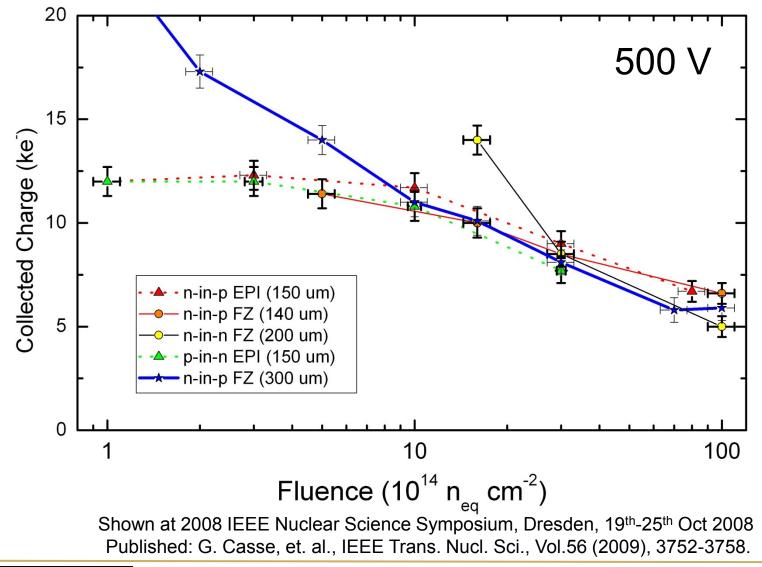
- Radiation damage from neutrons and protons appear to compensate for MCz material
 - Adds for FZ
- New mixed irradiations planned for n and p-bulk material to much higher fluences



Shown at 2009 IEEE Nuclear Science Symposium, Orlando, 25th-31st Oct 2009 Published: G. Casse, et. al., PoS(Vertex 2008) 036.

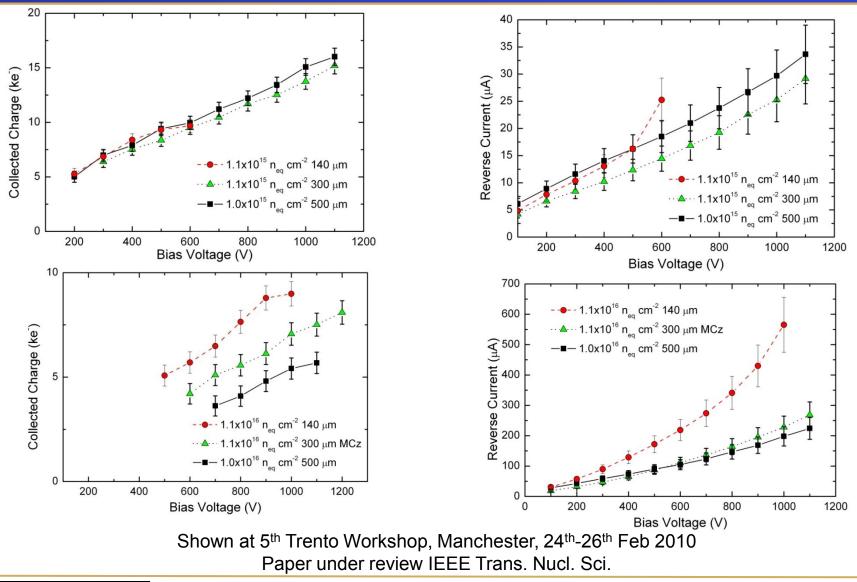


EPI/Thin Comparison





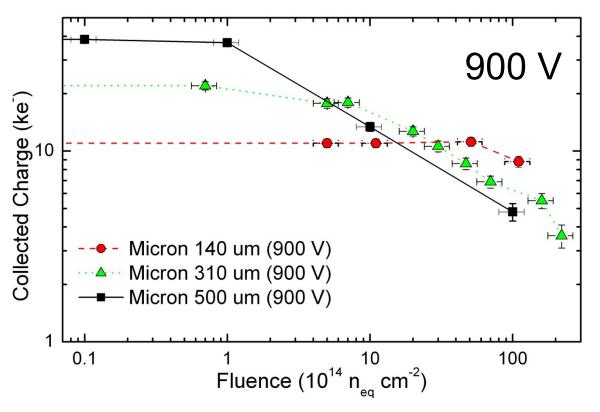
500 Micron Thick Sensors





Thickness Comparisons

- With same masks and base material (n-in-p FZ) used to make three thicknesses, a clear pattern emerges
 - At low fluences (<5×10¹⁴ n_{eq}cm⁻²), "classic" model of V_{FD}, n_{eff} and charge trapping holds
 - At higher fluences (3×10¹⁵ n_{eq}cm⁻²), "active" base and multiplication are dominant effects



Shown at 5th Trento Workshop, Manchester, 24th-26th Feb 2010 Paper under review IEEE Trans. Nucl. Sci.

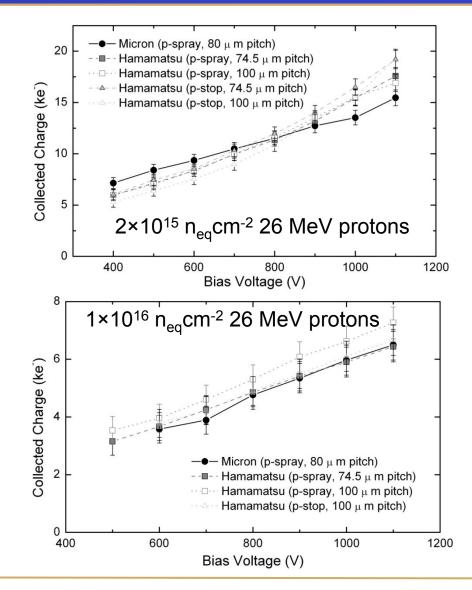
Below $5 \times 10^{14} n_{eq}$ cm⁻², charge advantage to being thicker Above $3 \times 10^{15} n_{eq}$ cm⁻², charge advantage to being thinner



P-stop/P-spray

- Used available ATLAS07 HPK minis to start study of the effects of manufacturer, isolation technique (stop/spray) and pitch on collected charge with highly irradiated devices
 - No measureable difference between HPK/Micron, stop/spray or pitch. Weird!

Shown at 5th Trento Workshop, Manchester, 24th-26th Feb 2010 Paper in draft





Conclusions

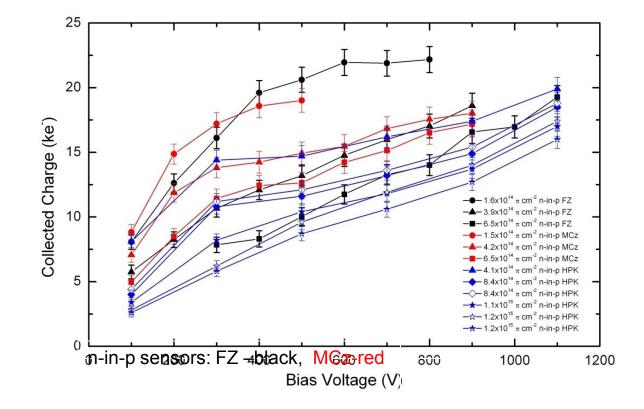
- Various detector configurations and bulk material types have been studied after neutron, pion, and proton irradiations
- With n-strip readout, bulk material type is important for collected charge at lower fluences (<1×10¹⁵ n_{eq}cm⁻²)
- At higher fluences (>3×10¹⁵ n_{eq}cm⁻²), the collected charge is fairly independent of bulk material type
 - Due to "active" base and charge multiplication
 - Bulk thickness is important with thinner devices yielding higher collected charge and reverse current
- With current RD50 devices, only mixed irradiations and n-in-n MCz after high neutron fluences (>2×10¹⁵ n_{eq}cm⁻²) studies left
- New Micron charge multiplication wafer and CNM trenched devices will allow for further study and hopefully design optimization for charge multiplication and "active" base effects



18

Pion Irradiations

- n-in-p
 - MCz better than
 FZ as expected



<u>Micron:</u> shown at TIPP09, Tsukuba, 12th-17th March 2009 published A. Affolder, et. al., Nucl. Instr. Meth. A, Vol.623 (2010), 177-179. <u>HPK:</u> New and unpublished Significant annealing during irradiation For highest doses, 13 days at 24 C°

